



STD3NM60N

N-channel 600 V, 1.6 Ω , 3.3 A, MDmesh™ II Power MOSFET in DPAK package

Datasheet — preliminary data

Features

Order codes	V _{DSS} @T _{Jmax}	R _{DS(on)} max.	I _D
STD3NM60N	650 V	< 1.8 Ω	3.3 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

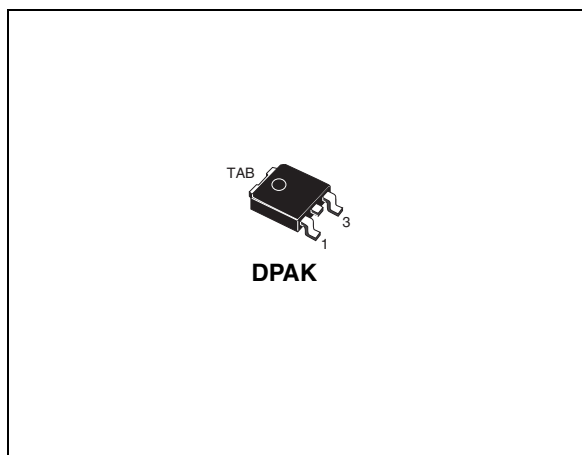


Figure 1. Internal schematic diagram

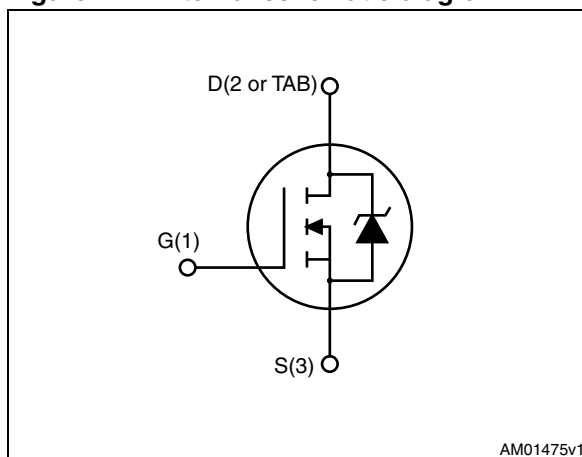


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD3NM60N	3NM60N	DPAK	Tape and reel

Contents

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate- source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	3.3	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	2.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	13	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	50	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_J T_{stg}	Operating junction temperature Storage temperature	- 55 to 150	$^\circ\text{C}$

1. Pulse width limited by safe operating area.

2. $I_{SD} \leq 3.3\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max	50	$^\circ\text{C}/\text{W}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max)	1	A
EAS	Single pulse avalanche energy (starting $T_J=25\text{ }^\circ\text{C}$, $I_D=I_{AR}$, $V_{DD}=50\text{ V}$)	86	mJ

2 Electrical characteristics

(T_{case} =25 °C unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0	600			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 600 V V _{DS} = 600 V, T _C =125 °C			1 100	μA μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 25 V; V _{DS} =0			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 1.65A		1.6	1.8	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0	-	188	-	pF
C _{oss}	Output capacitance			12.8		pF
C _{rss}	Reverse transfer capacitance			1.1		pF
C _{oss(tr)} ⁽¹⁾	Output capacitance time related	V _{DS} = 0, V _{GS} = 0	-	96.8	-	pF
R _g	Gate input resistance	f=1 MHz open drain	-	6	-	Ω
Q _g	Total gate charge	V _{DD} = 480 V, I _D = 3.3A, V _{GS} = 10 V <i>(see Figure 15)</i>	-	9.5	-	nC
Q _{gs}	Gate-source charge			2		nC
Q _{gd}	Gate-drain charge			5		nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 1.65\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ <i>(see Figure 14)</i>		6		ns
t_r	Rise time		-	9.5	-	ns
$t_{d(off)}$	Turn-off-delay time				23	ns
t_f	Fall time				31	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		3.3	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				13.2	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 3.3\text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 3.3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ <i>(see Figure 16)</i>	-	200		ns
Q_{rr}	Reverse recovery charge				910	nC
I_{RRM}	Reverse recovery current				9.1	A
t_{rr}	Reverse recovery time	$I_{SD} = 3.3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ <i>(see Figure 16)</i>	-	236		ns
Q_{rr}	Reverse recovery charge				1073	nC
I_{RRM}	Reverse recovery current				9.1	A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

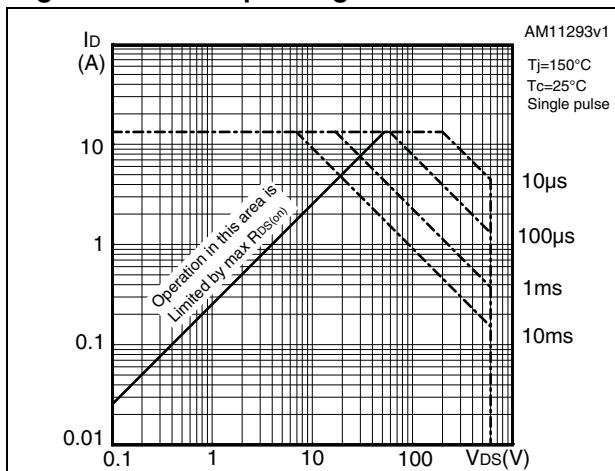


Figure 3. Thermal impedance

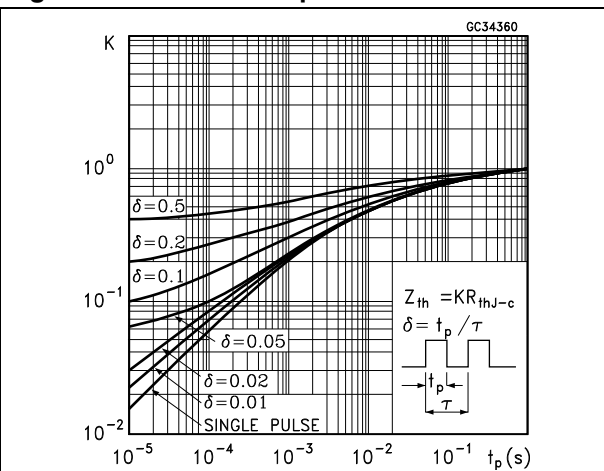


Figure 4. Output characteristics

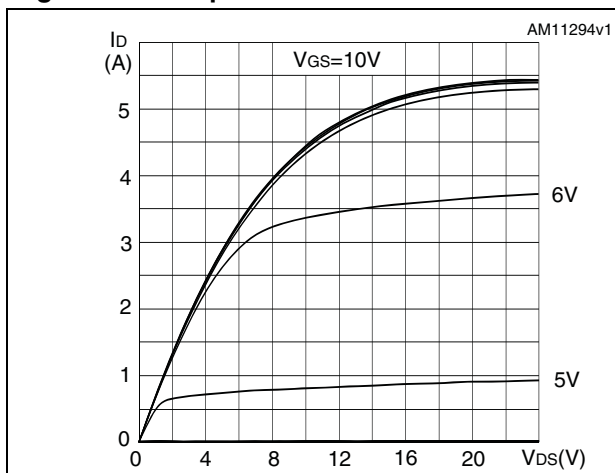


Figure 5. Transfer characteristics

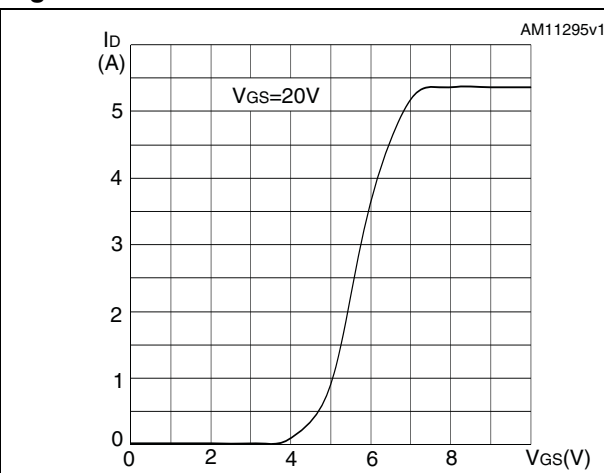


Figure 6. Gate charge vs gate-source voltage

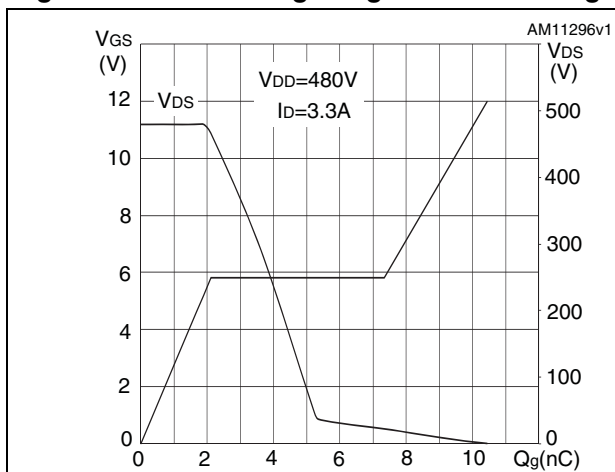


Figure 7. Static drain-source on-resistance

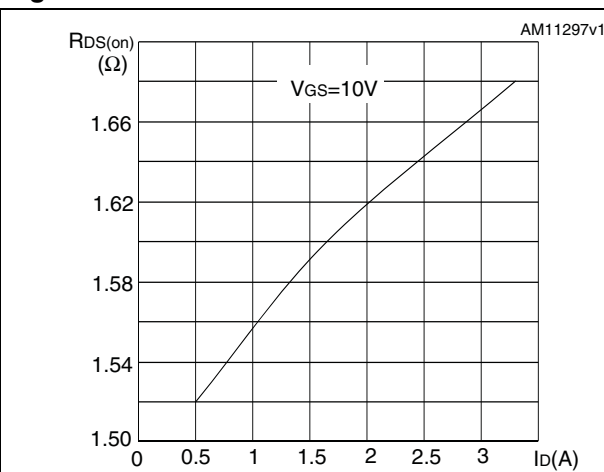


Figure 8. Capacitance variations

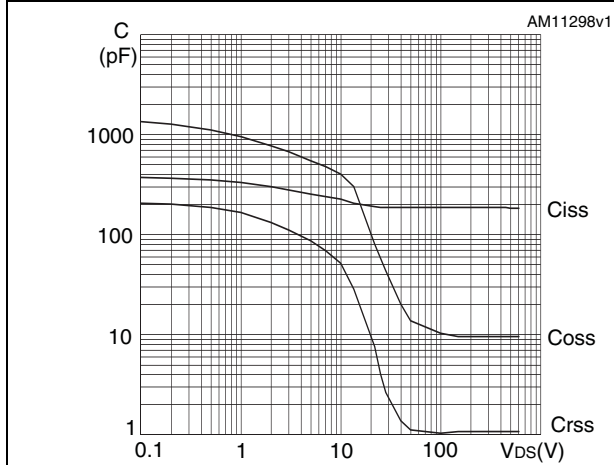


Figure 9. Output capacitance stored energy

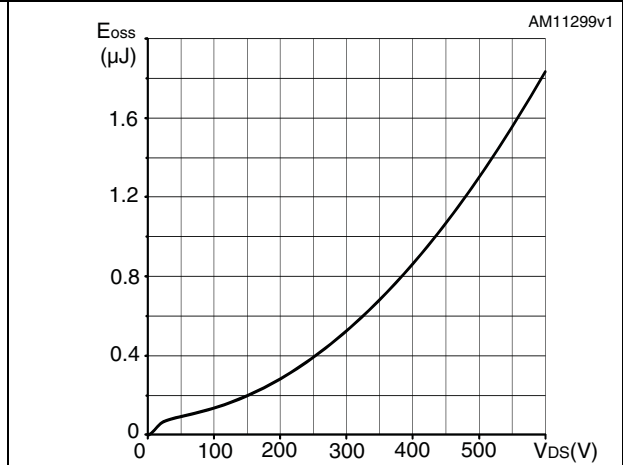


Figure 10. Normalized gate threshold voltage vs. temperature

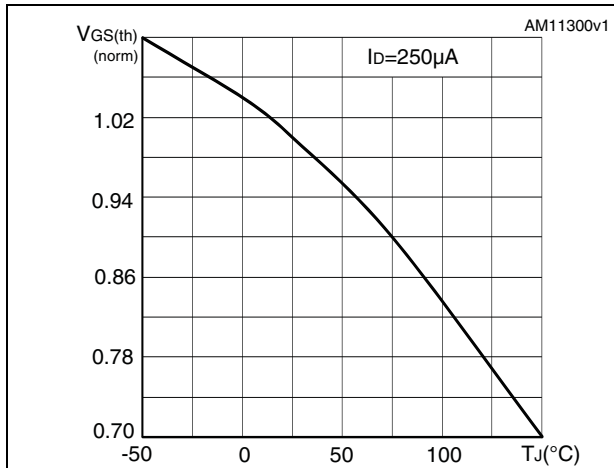


Figure 11. Normalized on-resistance vs. temperature

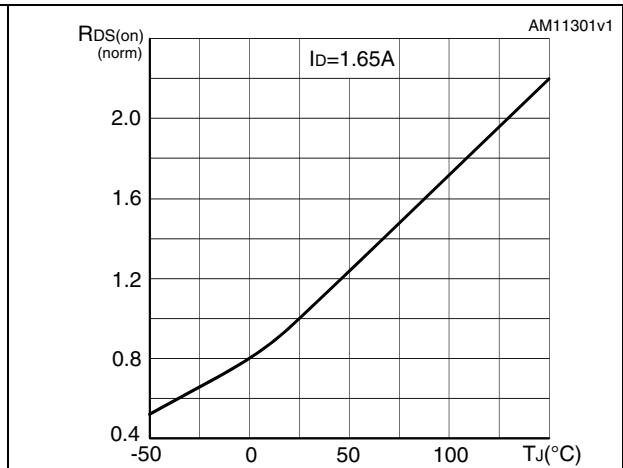


Figure 12. Source-drain diode forward characteristics

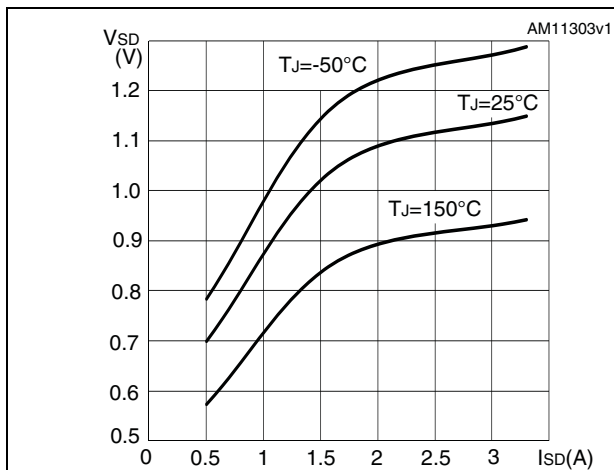
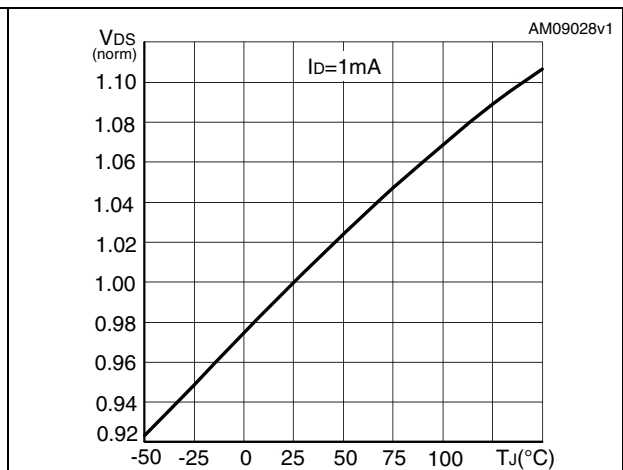
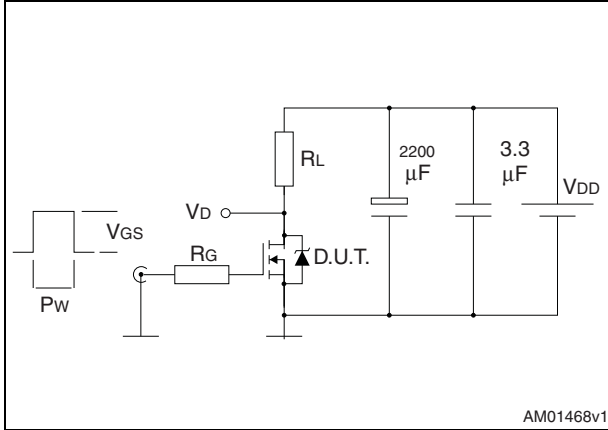


Figure 13. Normalized V_{DS} vs. temperature



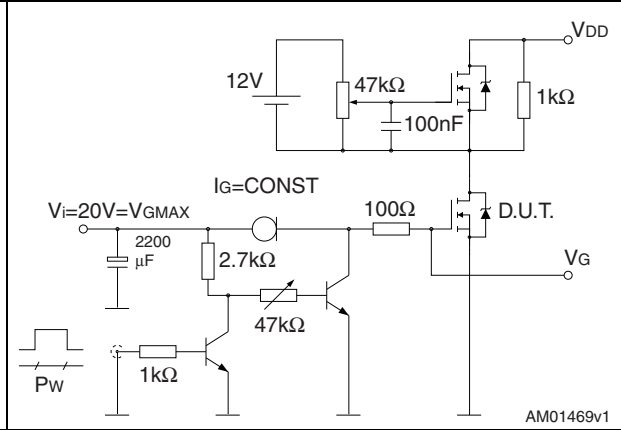
3 Test circuits

Figure 14. Switching times test circuit for resistive load



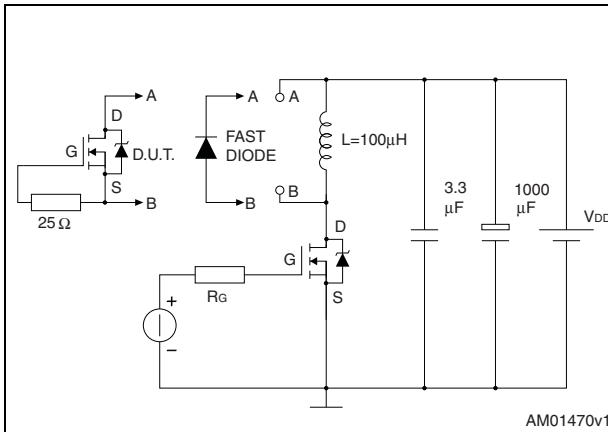
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Figure 15. Gate charge test circuit



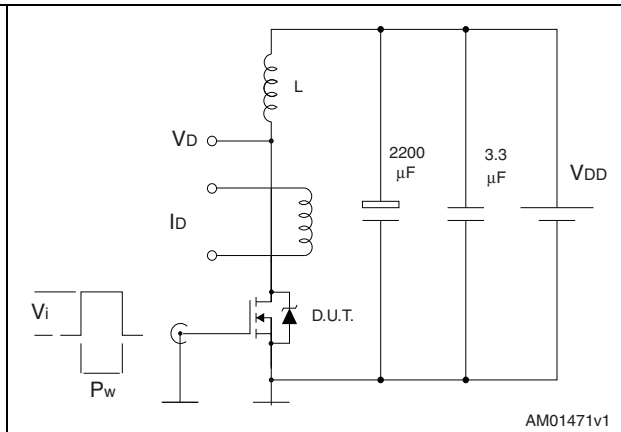
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Figure 16. Test circuit for inductive load switching and diode recovery times



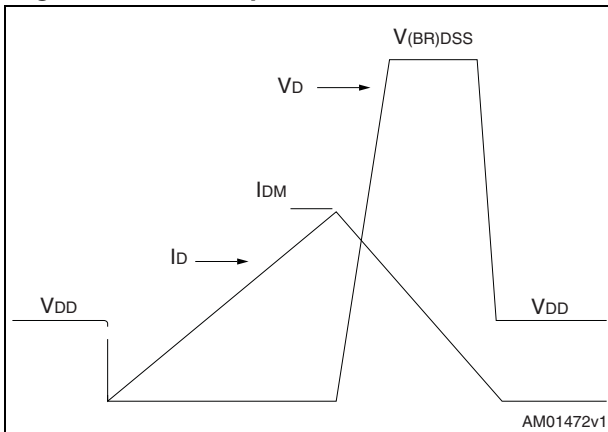
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Figure 17. Unclamped inductive load test circuit



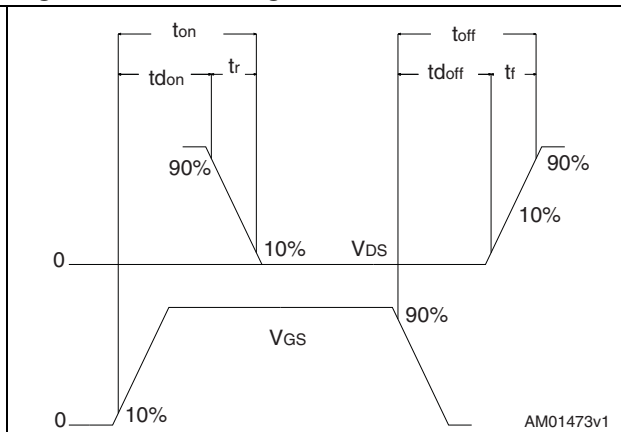
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Figure 18. Unclamped inductive waveform



AM01472v1

Figure 19. Switching time waveform



AM01473v1

4 Package mechanical data

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Table 9. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 20. DPAK (TO-252) drawing

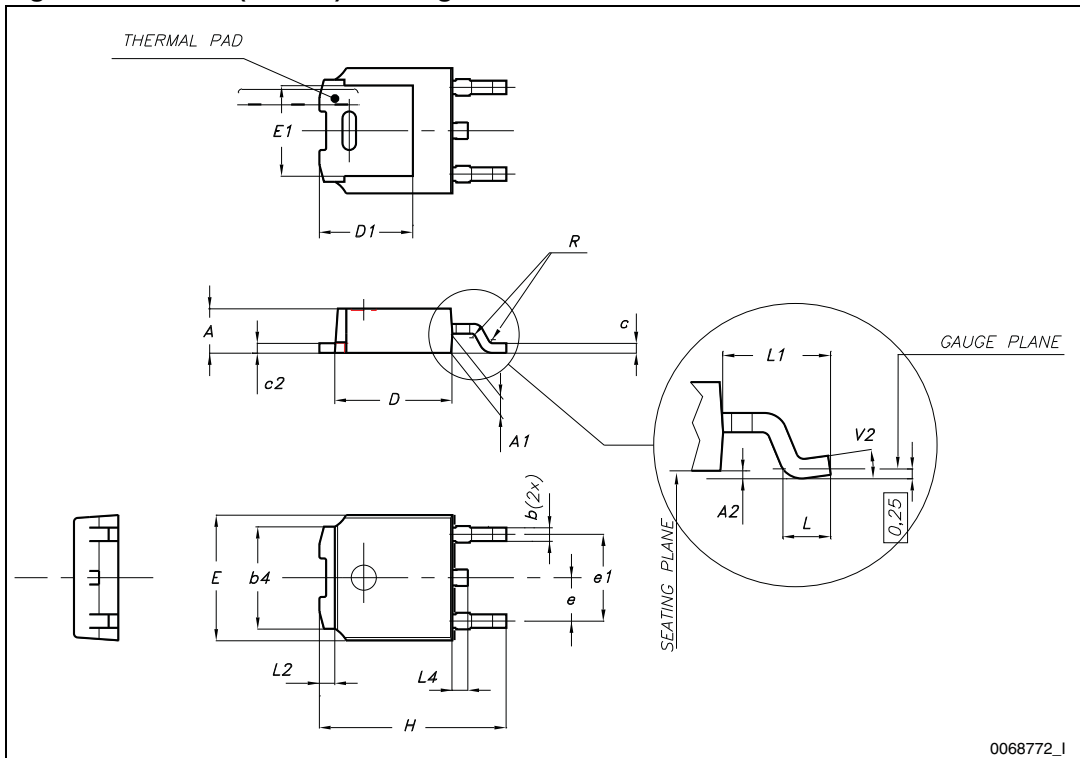
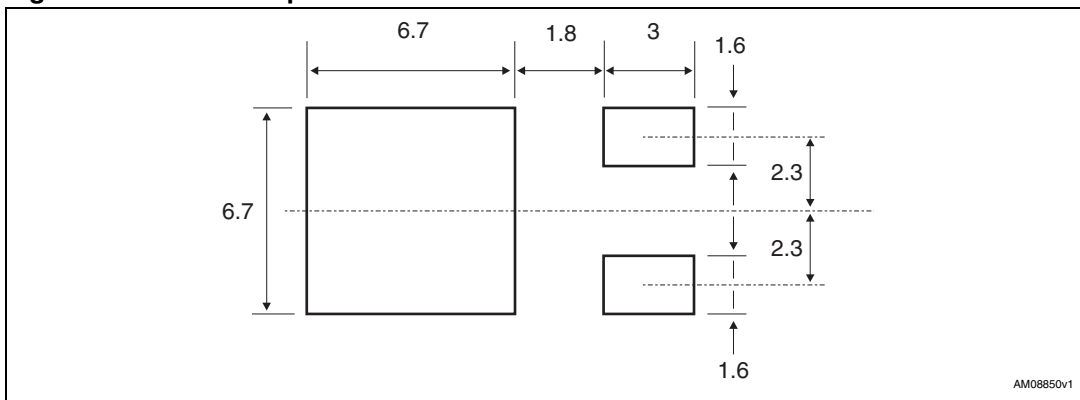


Figure 21. DPAK footprint^(a)



a. All dimensions are in millimeters

5 Packaging mechanical data

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 22. Tape for DPAK (TO-252)

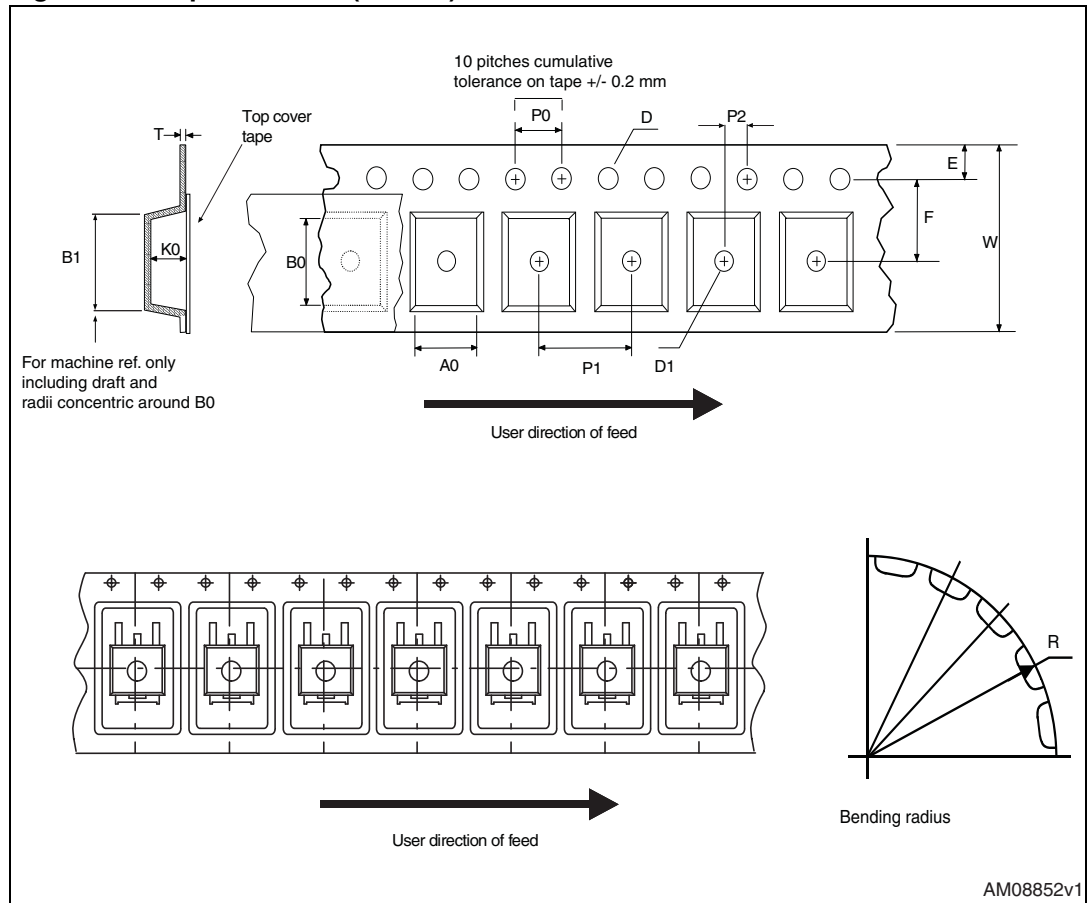
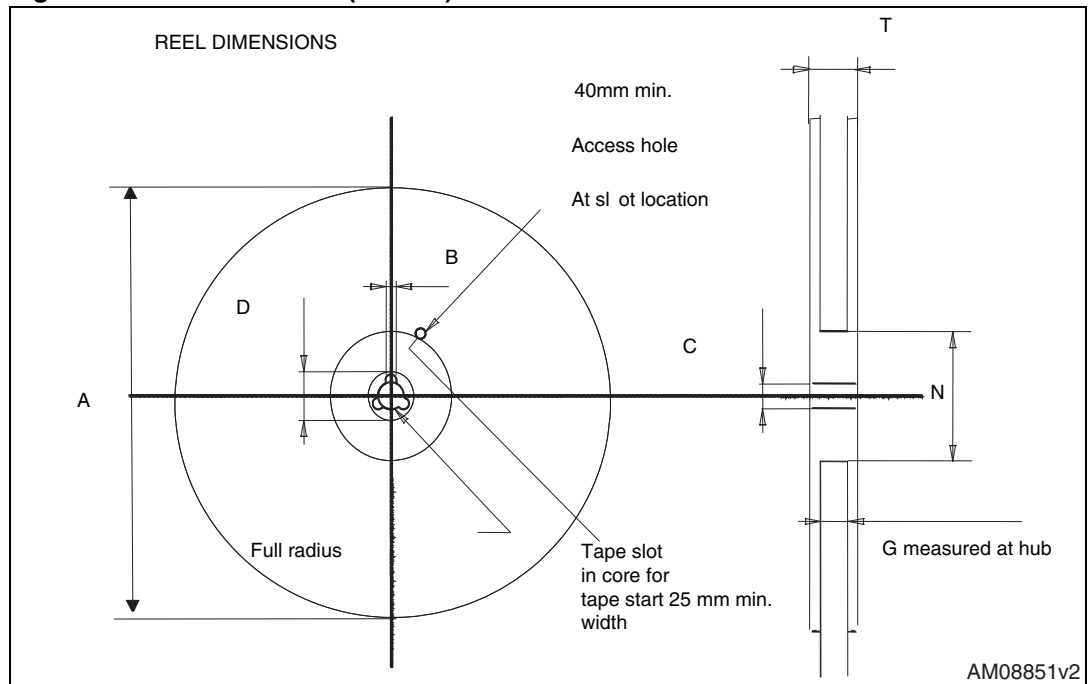


Figure 23. Reel for DPAK (TO-252)



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
10-May-2012	1	First release

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